

ABSTRACT

[00123] Briefly, devices and methods which may be used in conjunction with a Complementary Metal-Oxide Semiconductor (CMOS) process. Exemplary embodiments of the invention may provide an enhanced charge-pump circuit with gain compensation, an enhanced varactor with wide tuning range, and/or enhanced Phase-Lock Loop (PLL) circuits, which may be used, for example, within various oscillators and/or wireless communication devices.